

	Hits	Search Text	DBs
36	5	((ion near9 beam) or sputter\$4) same (voltage or "V")) and ((sputter\$4 near12 ion near4 beam) same (resist or photoresist) same (harden\$6 or cur\$3 or etch\$4resistant))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
37	2	((ion near9 beam) or sputter\$4) same RF same (voltage or "V" or volt)) and (sputter\$4 near12 ion near4 beam near16 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
38	4	((ion near9 beam) or sputter\$4) same (voltage or "V" or volt) same (photoresist or resist) same ("50V" "200V" "60V" "70V" "80V" "90V" "100V")) and ((sputter\$4 or (ion near4 beam)) near16 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
39	1	((ion near9 beam) or sputter\$4) same RF same (voltage or "V" or volt)) and (sputter\$4 near12 ion near4 beam near16 (resist or photoresist) same volt\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
40	4	((ion near9 beam) or sputter\$4) same (voltage or "V" or volt) same (photoresist or resist) same ("50V" "51V" "52V" "53V" "54V" "55V" "56V" "57V" "58V" "59V" "200V" "60V" "70V" "80V" "90V" "100V")) and ((sputter\$4 or (ion near4 beam)) near16 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
41	0	((ion near9 beam) or sputter\$4) same (voltage or "V" or volt) same (photoresist or resist) same ("S2V")) and ((sputter\$4 or (ion near4 beam)) near16 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
42	20	((ion near9 beam near19 sputter\$4) same (voltage or "V" or volt) same (photoresist or resist)) and ((sputter\$4 near26 ion near4 beam) near19 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
43	26	((ion near9 beam near19 sputter\$4) same (voltage or "V" or volt)) and ((sputter\$4 near26 ion near4 beam) near19 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
44	46	S49 NOT S48	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
45	23	((sputter\$4 near26 ion near4 beam) near19 (resist or photoresist)) same (harden\$4 or etch\$5resist\$4 or curable or cur\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
46	30	((ion near9 beam near19 sputter\$4) same (voltage or "V" or volt)) and ((sputter\$4 near26 ion near4 beam) near36 (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
47	76	((ion near9 beam near29 sputter\$4) same (voltage or "V" or volt)) and ((sputter\$4 near26 ion near4 beam) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
48	6	((sputter\$4 near26 ion near4 beam) same (resist or photoresist) same (harden\$4 or etch\$6resist\$4)) and (voltage or volt or "V")	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
49	8	((sputter\$4 near26 ion near4 beam) same (resist or photoresist) same (harden\$4 or etch\$6resist\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
50	53	((sputter\$4 near26 ion near6 beam) same (resist or photoresist) same (voltage or "V" or volt))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
51	53	((sputter\$4 near26 ion near6 beam) same (resist or photoresist) same (voltage or "V" or volt))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
52	76	((ion near9 beam near29 (ash\$4 or sputter\$4 or harden\$6 or curing)) same (voltage or "V" or volt)) and ((sputter\$4 near26 ion near4 beam) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
53	23	S56 NOT S55	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

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54	23	((ion near9 beam) same (ash\$4 or harden\$4 or (sputter\$4 near16 beam) or (sputter near9 etch\$4)) same (irradiat\$4 or imping\$4 or bombard\$6 or expos\$4) same (resist or photoresist or BARC or (organic near9 BARC) or (organic near9 resist) or (photosensitive near9 mask)) same (voltage or volt\$2 or "\$3V"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
55	702	((ion near9 beam) or ion) same (ash\$4 or harden\$4 or (sputter\$4 near16 beam) or (sputter near9 etch\$4) or imping\$4 or irradiat\$4 or bombard\$5) same (resist or photoresist or BARC or (organic near9 BARC) or (organic near9 resist) or (photosensitive near9 mask)) same (voltage or volt\$2 or "\$3V"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
56	44	((ion near9 beam) same (ash\$4 or harden\$4 or (sputter\$4 near16 beam) or (sputter near9 etch\$4)) same (resist or photoresist or BARC or (organic near9 BARC) or (organic near9 resist) or (photosensitive near9 mask)) same (voltage or volt\$2 or "\$3V"))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
57	658	S60 NOT S59	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

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58	24	S61 and ((resist or photoresist) same pattern same (etch near4 resist\$5))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
59	52	S61 and ((resist or photoresist) same pattern same ((etch near4 resist\$5) or harden\$5 or cured))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
60	87	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same ozone same (undercut\$4 or overhang or erod\$3 or etch\$4) same (concentration or amount or (flow near9 rate)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
61	30	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same ozone same (undercut\$4 or overhang or erod\$3 or etch\$4) same (concentration or amount or (flow near9 rate)) same (temperature or celsius or centigrade or heat\$4 or bak\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
62	35	((resist or photoresist) near19 (mask or pattern)) same ozone same (ash\$4 or imping\$4 or irradiat\$4 or introduc\$4 or expos\$4)) and ((photoresist or resist) same pattern) and (ozone near16 (concentration or amount or (flow near9 rate)) same (temperature or celsius or centigrade or heat\$4 or bak\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
63	2	(((resist or photoresist) near19 (mask or pattern)) same ozone same (ash\$4 or imping\$4 or irradiat\$4 or introduc\$4 or expos\$4)) and ((photoresist or resist) same pattern same (undercut\$4 or overhang or erod\$3 or etch\$4) same (harden\$4 or (etch near9 resist\$5))) and (ozone near16 (concentration or amount or (flow near9 rate)) same (temperature or celsius or centigrade or heat\$4 or bak\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB